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Title: **JP56007439A2: TREATING METHOD FOR SEMICONDUCTOR SUBSTRATE**

Country: JP Japan
Kind: A (See also: JP56007439B4)

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Applicant/Assignee:



SONY CORP

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Issued/Filed Dates:

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Application Number:

JP1979000083210

IPC Class:

H01L 21/324; H01L 21/265; H01L 21/268;

Priority Number(s):

June 29, 1979 JP1979000083210

Abstract:



Purpose: To prevent the generation of unnecessary thermal stress and pollution in a semiconductor element by a method wherein beams are locally irradiated only to fixed portions containing damaged regions and the portions are heated.

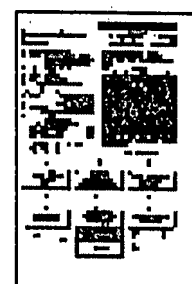
Constitution: Laser beams, etc. are irradiated to inactive regions having no effect on characteristics on a semiconductor wafer or element, and grid damage is given to the regions. The damaged regions 2 and their near regions are locally heated by laser beams 4, whose area are larger than the regions 2. In this case, the damaged regions 2 heated have gettering action, and the heating regions 5 near the regions 2 are clarified by gettering. According to this method, the diameters of thermic ray beams 3, 4 can arbitrarily be adjusted, and treatment is easy. When an element is formed at an appropriate location of the heating regions 5 except the damaged regions 2, its characteristic is excellent.

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Family: Show known family members

Other Abstract Info: none

Foreign References: No patents reference this one



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